## Towards a quantum resistance standard based on epita

Nature Nanotechnology 5, 186-189 DOI: 10.1038/nnano.2009.474

Citation Report

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123 124 125 126 127 128 129	Applications of Graphene., 2013,, 333-437.         Epitaxial Graphene Sensors for Detection of Small Magnetic Moments. IEEE Transactions on Magnetics, 2013, 49, 97-100.         Local breakdown of the quantum Hall effect in narrow single layer graphene Hall devices. Solid State Communications, 2013, 160, 47-51.         NO sensing one- and two-dimensional carbon nanostructures and nanohybrids: Progress and perspectives. Sensors and Actuators B: Chemical, 2013, 181, 9-21.         Robust Graphene Membranes in a Silicon Carbide Frame. ACS Nano, 2013, 7, 4441-4448.         Graphene transparent electrodes grown by rapid chemical vapor deposition with ultrathin indium tin oxide contact layers for GaN light emitting diodes. Applied Physics Letters, 2013, 102, .         Growth of large area monolayer graphene on 3C-SiC and a comparison with other SiC polytypes. Carbon, 2013, 57, 477-484.	1.2 0.9 4.0 7.3 1.5 5.4	9 13 3 34 15 39
<ul> <li>123</li> <li>124</li> <li>125</li> <li>126</li> <li>127</li> <li>128</li> <li>129</li> <li>130</li> </ul>	Applications of Craphene. , 2013, , 333-437.         Epitaxial Graphene Sensors for Detection of Small Magnetic Moments. IEEE Transactions on Magnetics, 2013, 49, 97-100.         Local breakdown of the quantum Hall effect in narrow single layer graphene Hall devices. Solid State Communications, 2013, 160, 47-51.         NO sensing one- and two-dimensional carbon nanostructures and nanohybrids: Progress and perspectives. Sensors and Actuators B: Chemical, 2013, 181, 9-21.         Robust Graphene Membranes in a Silicon Carbide Frame. ACS Nano, 2013, 7, 4441-4448.         Graphene transparent electrodes grown by rapid chemical vapor deposition with ultrathin indium tin oxide contact layers for GaN light emitting diodes. Applied Physics Letters, 2013, 102, .         Growth of large area monolayer graphene on 3C-SiC and a comparison with other SiC polytypes. Carbon, 2013, 57, 477-484.         On the Differing Sensitivity to Chemical Gating of Single and Double Layer Epitaxial Graphene Explored Using Scanning Kelvin Probe Microscopy. ACS Nano, 2013, 7, 4647-4656.	1.2 0.9 4.0 7.3 1.5 5.4 7.3	9 13 3 3 4 15 39 100 38

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